

DESCRIPTION

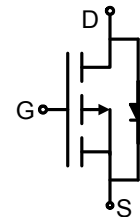
The SSF2449 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

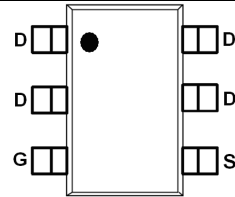
- $V_{DS} = -20V, I_D = -5A$
 $R_{DS(ON)} < 100m\Omega @ V_{GS} = -2.5V$
 $R_{DS(ON)} < 60m\Omega @ V_{GS} = -4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Application

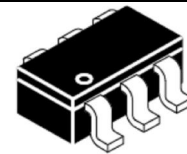
- PWM applications
- Load switch
- Power management



Schematic diagram



Pin Assignment



TSOP-6 top view

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2449	SSF2449	TSOP-6	—	—	—

ABSOLUTE MAXIMUM RATINGS($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I_D	-5	A
	I_{DM}	-20	A
Maximum Power Dissipation	P_D	1.2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	110	$^\circ C/W$
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ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$			-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$			± 100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.6		-1	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-5A$		49	60	m Ω
		$V_{GS}=-2.5V, I_D=-3A$		83	100	
Forward Transconductance	g_{FS}	$V_{DS}=-10V, I_D=-5A$		9		S

DYNAMIC CHARACTERISTICS (Note4)

Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V, F=1.0MHz$		610		PF
Output Capacitance	C_{oss}			130		PF
Reverse Transfer Capacitance	C_{rss}			100		PF

SWITCHING CHARACTERISTICS (Note 4)

Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-10V, I_D=-5A, V_{GS}=-4.5V, R_{GEN}=1\Omega$		27		nS
Turn-on Rise Time	t_r			60		nS
Turn-Off Delay Time	$t_{d(off)}$			30		nS
Turn-Off Fall Time	t_f			10		nS
Total Gate Charge	Q_g	$V_{DS}=-10V, I_D=-5A, V_{GS}=-4.5V$		9.6		nC
Gate-Source Charge	Q_{gs}			1.5		nC
Gate-Drain Charge	Q_{gd}			2.4		nC

DRAIN-SOURCE DIODE CHARACTERISTICS

Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-1.7A$			-1.2	V
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NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

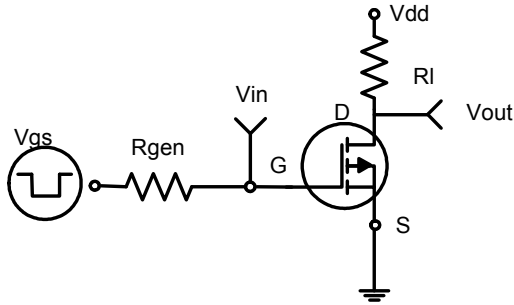


Figure1:Switching Test Circuit

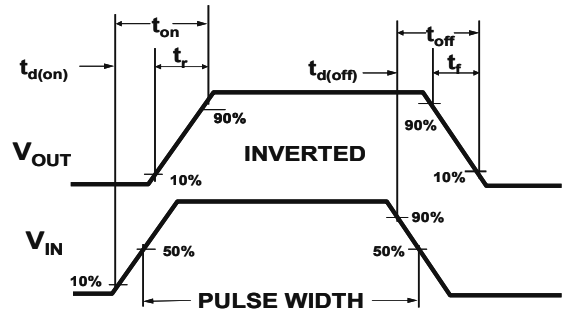


Figure 2:Switching Waveforms

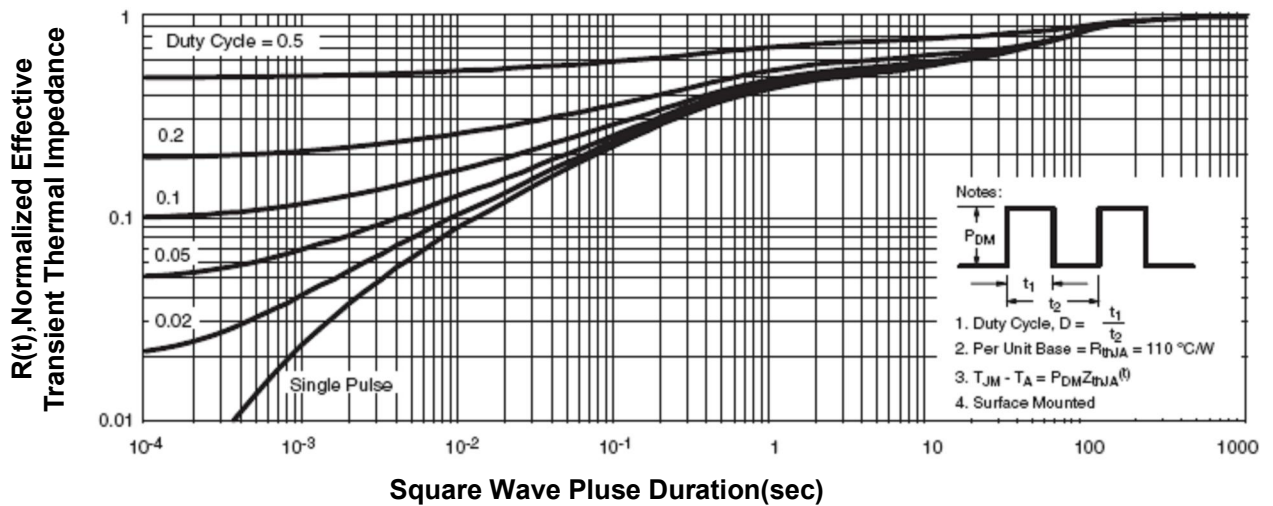
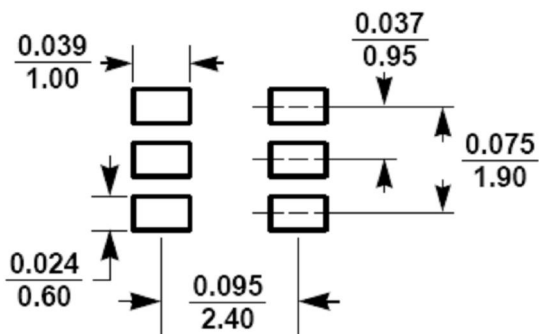
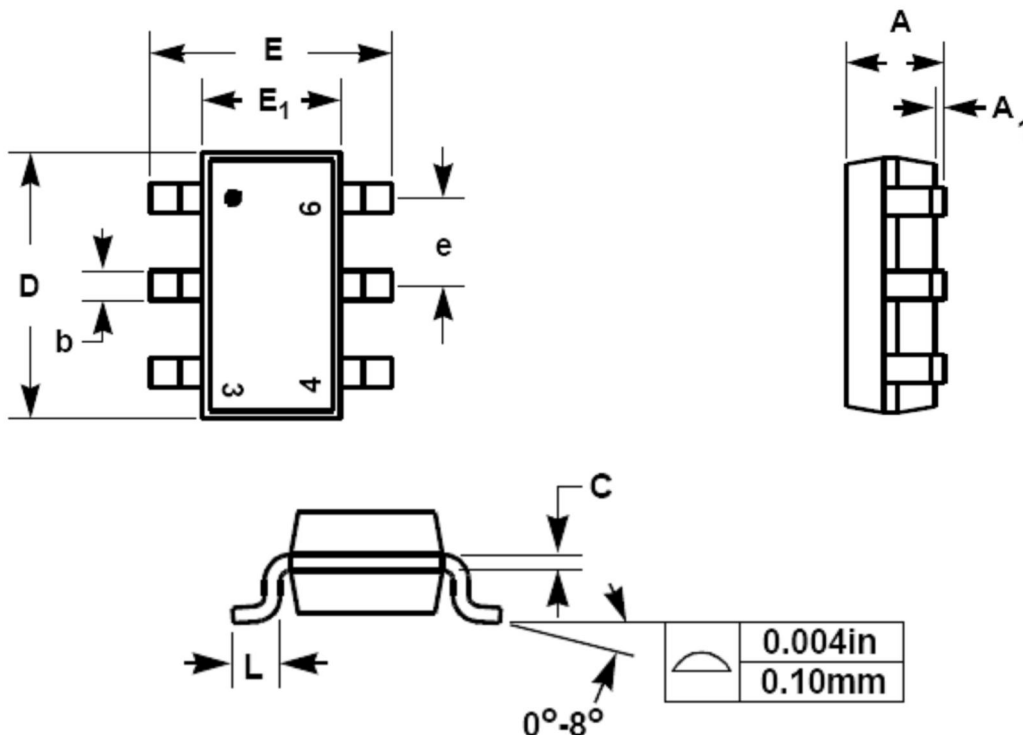


Figure 3: Normalized Maximum Transient Thermal Impedance

TSOP-6 PACKAGE INFORMATION



SYMBOL	Millimeters	
	MIN	MAX
A	0.90	1.10
A1	0.10	
b	0.30	0.50
c	0.08	0.20
D	2.70	3.10
E	2.60	3.00
E1	1.40	1.80
e	0.95 BSC	
L	0.35	0.55

NOTES:

1. Dimensions are inclusive of plating
2. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 6 mils.
3. Dimension L is measured in gauge plane.
4. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.